

10/787123

C/C



Docket No.: M4065.1006/P1006-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Terry L. Gilton

Patent No.: 7,132,675

Issued: November 7, 2006

For: PROGRAMMABLE CONDUCTOR
MEMORY CELL STRUCTURE AND
METHOD THEREFOR

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
NOV 30 2006
of Correction

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the Other Publications portion of the References Cited section, the PTO made the following errors to be corrected:

"Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system $\text{Se}_{75}\text{Ge}_{25-x}\text{Sb}_x$, Appl. Phys. A 55 (1992) 167-169."

Should read

--Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system $\text{Se}_{75}\text{Ge}_{25-x}\text{Sb}_x$, Appl. Phys. A 55 (1992) 167-169.--;

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DSMDB-2176936v01

"Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B 74 (1996) 37-50."

Should read

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"Joullie, A.M.; Marruchi, J., On the DC electrical conduction of amorphous As₂Se₇ before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109."

Should read

--Joullie, A.M.; Marruchi, J., On the DC electrical conduction of amorphous As₂Se₇ before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.--;

"Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japn. J. Appl. Phys. 26 (1987) 15-21."

Should read

--Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japn. J. Appl. Phys. 26 (1987) 15-21.--; and

"Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223."

Should read

--Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.--.

In the Specification, the PTO made the following error to be corrected:

Column 4, line 9, "additionlly" should read --additionally--.

The errors were not in the application as filed or amended by applicant; accordingly no fee is required.

DEC 01 2006

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

Dated: November 28, 2006

Respectfully submitted,

By 

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,132,675
APPLICATION NO. : 10/787,123
ISSUE DATE : November 7, 2006
INVENTOR : Terry L. Gilton

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Other Publications portion of the References Cited section, the following errors are corrected:

"Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system $\text{Se}_{75}\text{Ge}_{25-x}\text{Sb}_x$, Appl. Phys. A 55 (1992) 167-169."

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"Joullie, A.M.; Marruchi, J., On the DC electrical conduction of amorphous As_2Se_7 before swiching, Phys. Stat. Sol. (a) 13 (1972) K105-K109."

Should read

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DSMDB-2176932v01

--Joullie, A.M.; Marruchi, J., On the DC electrical conduction of amorphous As_2Se_7 before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.--;

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